



## LM2705 Micropower Step-Up DC-DC Converter With 150-mA Peak Current Limit

### 1 Features

- 2.2-V to 7-V Input Range
- 150-mA, 0.7- $\Omega$  Internal Switch
- Adjustable Output Voltage up to 20 V
- Input Undervoltage Lockout
- 0.01- $\mu$ A Shutdown Current
- Uses Small Surface-Mount Components
- Small 5-Pin SOT-23 Package

### 2 Applications

- LCD Bias Supplies
- White-LED Backlighting
- Handheld Devices
- Digital Cameras
- Portable Applications

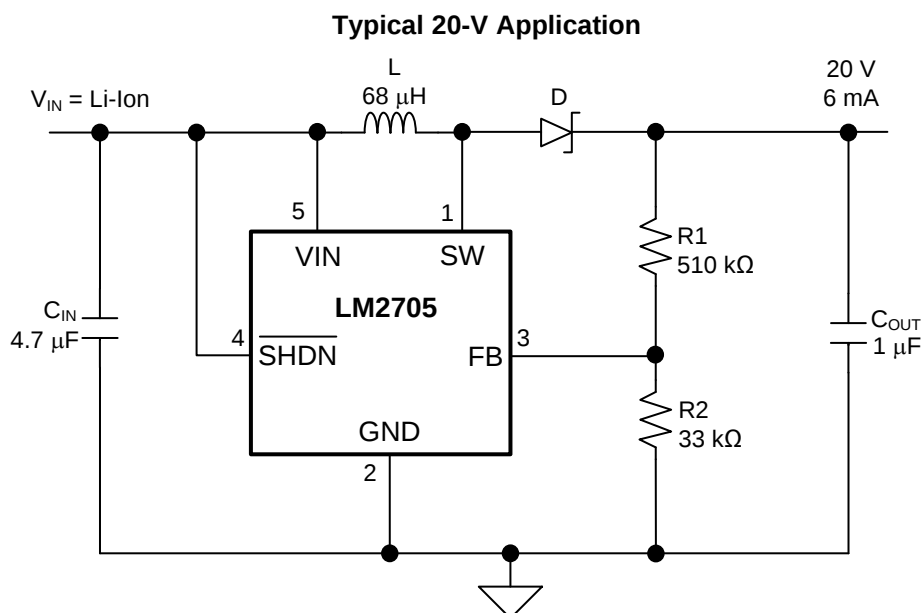
### 3 Description

The LM2705 is a micropower step-up DC-DC converter in a small 5-pin SOT-23 package. A current-limited, fixed-off-time control scheme conserves operating current, which results in high efficiency over a wide range of load conditions. The 21-V switch allows for output voltages as high as 20 V. The low 400-ns off-time permits the use of tiny, low-profile inductors and capacitors to minimize footprint and cost in space-conscious portable applications. The LM2705 is ideal for LCD panels requiring low current and high efficiency as well as white-LED applications for cellular phone backlighting. The LM2705 device can drive up to 3 white LEDs from a single Li-Ion battery. The low peak-inductor current of the LM2705 makes it ideal for USB applications.

#### Device Information<sup>(1)</sup>

| PART NUMBER | PACKAGE    | BODY SIZE (NOM)          |
|-------------|------------|--------------------------|
| LM2705      | SOT-23 (5) | 2.90 mm $\times$ 1.60 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.



Copyright © 2016, Texas Instruments Incorporated



## Table of Contents

|                                                |          |                                                      |           |
|------------------------------------------------|----------|------------------------------------------------------|-----------|
| <b>1 Features</b> .....                        | <b>1</b> | <b>8 Application and Implementation</b> .....        | <b>9</b>  |
| <b>2 Applications</b> .....                    | <b>1</b> | 8.1 Application Information.....                     | 9         |
| <b>3 Description</b> .....                     | <b>1</b> | 8.2 Typical Application .....                        | 9         |
| <b>4 Revision History</b> .....                | <b>2</b> | 8.3 Additional Applications.....                     | 12        |
| <b>5 Pin Configuration and Functions</b> ..... | <b>3</b> | <b>9 Power Supply Recommendations</b> .....          | <b>15</b> |
| <b>6 Specifications</b> .....                  | <b>4</b> | <b>10 Layout</b> .....                               | <b>15</b> |
| 6.1 Absolute Maximum Ratings .....             | 4        | 10.1 Layout Guidelines .....                         | 15        |
| 6.2 ESD Ratings.....                           | 4        | 10.2 Layout Example .....                            | 15        |
| 6.3 Recommended Operating Conditions.....      | 4        | <b>11 Device and Documentation Support</b> .....     | <b>16</b> |
| 6.4 Thermal Information .....                  | 4        | 11.1 Device Support.....                             | 16        |
| 6.5 Electrical Characteristics.....            | 5        | 11.2 Receiving Notification of Documentation Updates | 16        |
| 6.6 Typical Characteristics .....              | 6        | 11.3 Community Resources.....                        | 16        |
| <b>7 Detailed Description</b> .....            | <b>8</b> | 11.4 Trademarks .....                                | 16        |
| 7.1 Overview .....                             | 8        | 11.5 Electrostatic Discharge Caution.....            | 16        |
| 7.2 Functional Block Diagram .....             | 8        | 11.6 Glossary .....                                  | 16        |
| 7.3 Feature Description.....                   | 8        | <b>12 Mechanical, Packaging, and Orderable</b>       | <b>16</b> |
| 7.4 Device Functional Modes.....               | 8        | <b>Information</b> .....                             | <b>16</b> |

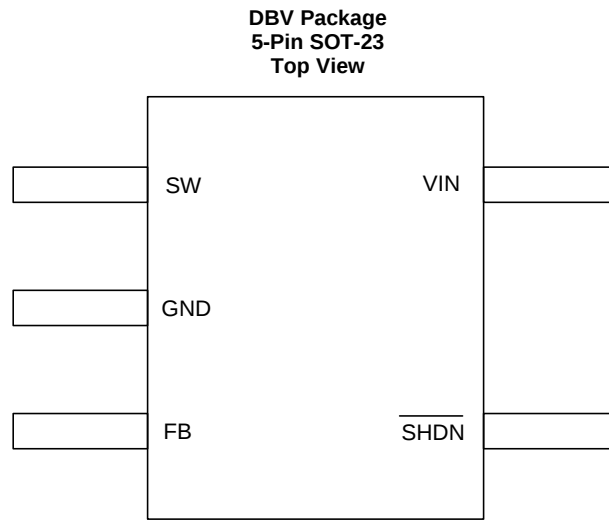
## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

| Changes from Revision E (May 2013) to Revision F                                                                                                                                                                                                                                                                                                                                                                                 | Page |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|
| • Added <i>Device Information</i> and <i>Pin Configuration and Functions</i> sections, <i>ESD Ratings</i> and <i>Thermal Information</i> tables, <i>Feature Description</i> , <i>Device Functional Modes</i> , <i>Application and Implementation</i> , <i>Power Supply Recommendations</i> , <i>Layout</i> , <i>Device and Documentation Support</i> , and <i>Mechanical, Packaging, and Orderable Information</i> sections..... | 1    |
| • Deleted pin definition list - added content to <i>Pin Functions</i> .....                                                                                                                                                                                                                                                                                                                                                      | 3    |
| • Changed $R_{\theta JA}$ value from "220°C/W" to "164.9°C/W" .....                                                                                                                                                                                                                                                                                                                                                              | 4    |

| Changes from Revision D (May 2013) to Revision E                        | Page |
|-------------------------------------------------------------------------|------|
| • Changed layout of National Semiconductor data sheet to TI format..... | 14   |

## 5 Pin Configuration and Functions



### Pin Functions

| PIN |                          | TYPE  | DESCRIPTION                                                                                                                                      |
|-----|--------------------------|-------|--------------------------------------------------------------------------------------------------------------------------------------------------|
| NO. | NAME                     |       |                                                                                                                                                  |
| 1   | SW                       | Input | Power switch input. This is the drain of the internal NMOS power switch. Minimize the metal trace area connected to this pin to minimize EMI.    |
| 2   | GND                      | —     | Ground - tie directly to ground plane.                                                                                                           |
| 3   | FB                       | Input | Output voltage feedback input — set the output voltage by selecting values for R1 and R2 using: $R1 = R2 \times (V_{OUT} / 1.237 \text{ V}) - 1$ |
| 4   | $\overline{\text{SHDN}}$ | Input | Active low shutdown - drive this pin to > 1.1 V to enable the device. Drive this pin to < 0.3 V to lase the device in a low-power shutdown.      |
| 5   | VIN                      | Input | Analog and power input supply pin                                                                                                                |

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

|                                                             | MIN                      | MAX | UNIT |
|-------------------------------------------------------------|--------------------------|-----|------|
| V <sub>IN</sub>                                             |                          | 7.5 | V    |
| SW voltage                                                  |                          | 21  | V    |
| FB voltage                                                  |                          | 2   | V    |
| SHDN voltage                                                |                          | 7.5 | V    |
| Maximum junction temperature, T <sub>J</sub> <sup>(3)</sup> |                          | 150 | °C   |
| Lead temperature                                            | Soldering (10 seconds)   | 300 | °C   |
|                                                             | Vapor phase (60 seconds) | 215 | °C   |
|                                                             | Infrared (15 seconds)    | 220 | °C   |
| Storage temperature, T <sub>stg</sub>                       | –65                      | 150 | °C   |

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) If Military/Aerospace specified devices are required, contact the TI Sales Office/Distributors for availability and specifications.
- (3) The maximum allowable power dissipation is a function of the maximum junction temperature, T<sub>J(MAX)</sub>, the junction-to-ambient thermal resistance, R<sub>θJA</sub>, and the ambient temperature, T<sub>A</sub>. See *Thermal Information* for the thermal resistance. The maximum allowable power dissipation at any ambient temperature is calculated using:  $P_{D(MAX)} = (T_{J(MAX)} - T_A) / R_{\theta JA}$ . Exceeding the maximum allowable power dissipation will cause excessive die temperature.

### 6.2 ESD Ratings

|                                            | VALUE                                                             | UNIT  |
|--------------------------------------------|-------------------------------------------------------------------|-------|
| V <sub>(ESD)</sub> Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup> | ±2000 |
|                                            | Machine model <sup>(2)</sup>                                      | ±200  |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) ESD susceptibility using the machine model is 150 V for SW pin.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|                                     | MIN | NOM | MAX  | UNIT |
|-------------------------------------|-----|-----|------|------|
| Supply voltage                      | 2.2 |     | 7    | V    |
| SW voltage, maximum                 |     |     | 20.5 | V    |
| Junction temperature <sup>(1)</sup> | –40 |     | 125  | °C   |

- (1) All limits specified at room temperature and at *temperature extremes*. All room temperature limits are 100% production tested or specified through statistical analysis. All limits at temperature extremes are specified via correlation using standard statistical quality control (SQC) methods. All limits are used to calculate average outgoing quality level (AOQL).

### 6.4 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |                                              | LM2705       | UNIT |
|-------------------------------|----------------------------------------------|--------------|------|
|                               |                                              | DBV (SOT-23) |      |
|                               |                                              | 5 PINS       |      |
| R <sub>θJA</sub>              | Junction-to-ambient thermal resistance       | 164.9        | °C/W |
| R <sub>θJC(top)</sub>         | Junction-to-case (top) thermal resistance    | 116.8        | °C/W |
| R <sub>θJB</sub>              | Junction-to-board thermal resistance         | 27.8         | °C/W |
| ψ <sub>JT</sub>               | Junction-to-top characterization parameter   | 13.6         | °C/W |
| ψ <sub>JB</sub>               | Junction-to-board characterization parameter | 27.3         | °C/W |

- (1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics*.

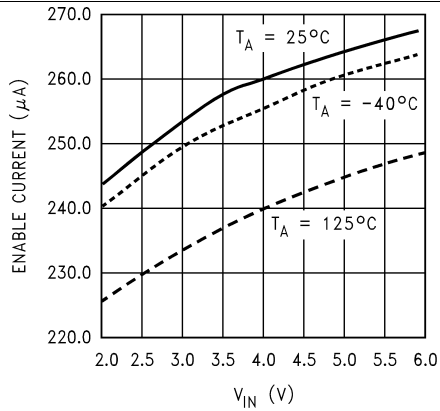
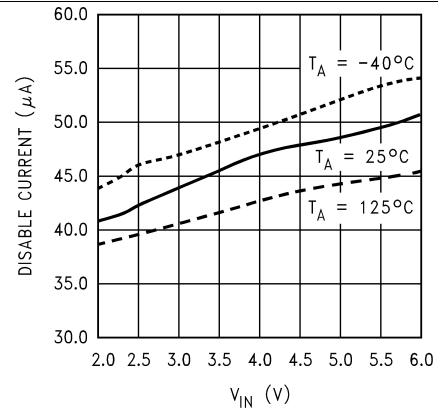
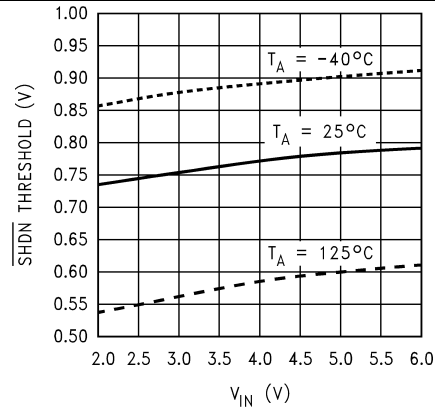
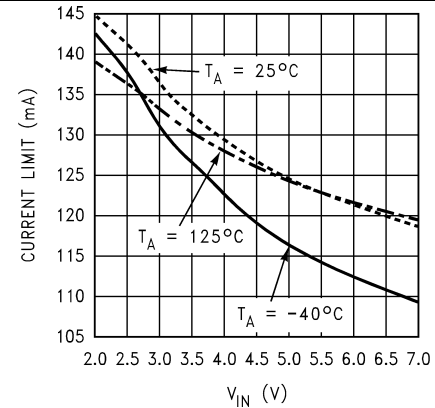
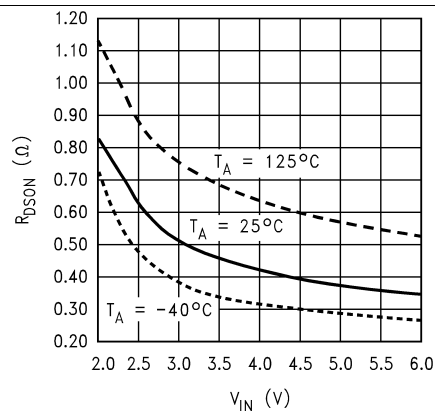
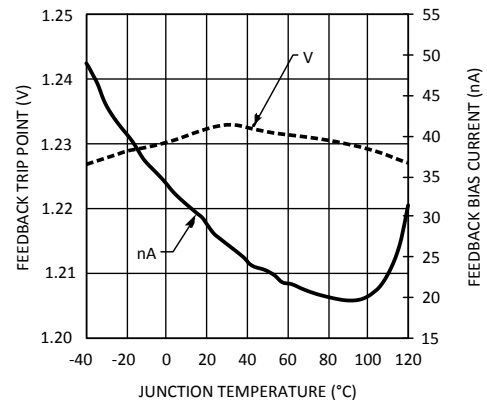
## 6.5 Electrical Characteristics

Unless otherwise specified, specifications apply for  $T_J = 25^\circ\text{C}$  and  $V_{IN} = 2.2\text{ V}$ .

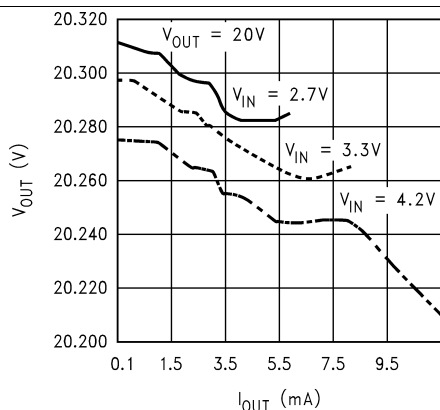
| PARAMETER                          |                                      | TEST CONDITIONS                                                        | MIN <sup>(1)</sup> | TYP <sup>(2)</sup> | MAX <sup>(1)</sup> | UNIT          |
|------------------------------------|--------------------------------------|------------------------------------------------------------------------|--------------------|--------------------|--------------------|---------------|
| $I_Q$                              | Device disabled                      | FB = 1.3 V                                                             |                    | 40                 |                    | $\mu\text{A}$ |
|                                    |                                      | FB = 1.3 V, $-40^\circ\text{C}$ to $125^\circ\text{C}$                 |                    |                    | 70                 |               |
|                                    | Device enabled                       | FB = 1.2 V                                                             |                    | 235                |                    |               |
|                                    |                                      | FB = 1.2 V, $-40^\circ\text{C}$ to $125^\circ\text{C}$                 |                    |                    | 300                |               |
|                                    | Shutdown                             | $\overline{\text{SHDN}} = 0\text{ V}$                                  |                    | 0.01               | 2.5                |               |
| $V_{FB}$                           | Feedback trip point                  |                                                                        |                    | 1.237              |                    | V             |
|                                    |                                      | $-40^\circ\text{C}$ to $125^\circ\text{C}$                             | 1.189              |                    | 1.269              |               |
| $I_{CL}$                           | Switch current limit                 |                                                                        |                    | 150                |                    | mA            |
|                                    |                                      | $-40^\circ\text{C}$ to $125^\circ\text{C}$                             | 100                |                    | 180                |               |
| $I_B$                              | FB pin bias current                  | FB = 1.23 V <sup>(3)</sup>                                             |                    | 30                 |                    | nA            |
|                                    |                                      | FB = 1.23 V, $-40^\circ\text{C}$ to $125^\circ\text{C}$ <sup>(3)</sup> |                    |                    | 120                |               |
| $V_{IN}$                           | Input voltage                        | $-40^\circ\text{C}$ to $125^\circ\text{C}$                             | 2.2                |                    | 7                  | V             |
| $R_{DS(on)}$                       | Switch $R_{DS(on)}$                  |                                                                        |                    | 0.7                |                    | $\Omega$      |
|                                    |                                      | $-40^\circ\text{C}$ to $125^\circ\text{C}$                             |                    |                    | 1.6                |               |
| $T_{OFF}$                          | Switch off time                      |                                                                        |                    | 400                |                    | ns            |
| $I_{SD}$                           | $\overline{\text{SHDN}}$ pin current | $\overline{\text{SHDN}} = V_{IN}$ , $T_J = 25^\circ\text{C}$           |                    | 0                  | 80                 | nA            |
|                                    |                                      | $\overline{\text{SHDN}} = V_{IN}$ , $T_J = 125^\circ\text{C}$          |                    | 15                 |                    |               |
|                                    |                                      | $\overline{\text{SHDN}} = \text{GND}$                                  |                    | 0                  |                    |               |
| $I_L$                              | Switch leakage current               | $V_{SW} = 20\text{ V}$                                                 |                    | 0.05               | 5                  | $\mu\text{A}$ |
| UVP                                | Input undervoltage lockout           | ON/OFF threshold                                                       |                    | 1.8                |                    | V             |
| $V_{FB}$ hysteresis                | Feedback hysteresis                  |                                                                        |                    | 8                  |                    | mV            |
| $\overline{\text{SHDN}}$ threshold | $\overline{\text{SHDN}}$ low         |                                                                        |                    | 0.7                |                    | V             |
|                                    |                                      | $-40^\circ\text{C}$ to $125^\circ\text{C}$                             |                    |                    | 0.3                |               |
|                                    | $\overline{\text{SHDN}}$ high        |                                                                        |                    | 0.7                |                    |               |
|                                    |                                      | $-40^\circ\text{C}$ to $125^\circ\text{C}$                             | 1.1                |                    |                    |               |

- (1) All limits specified at room temperature and at *temperature extremes*. All room temperature limits are 100% production tested or specified through statistical analysis. All limits at temperature extremes are specified via correlation using standard statistical quality control (SQC) methods. All limits are used to calculate average outgoing quality level (AOQL).
- (2) Typical numbers are at  $25^\circ\text{C}$  and represent the most likely norm.
- (3) Feedback current flows into the pin.

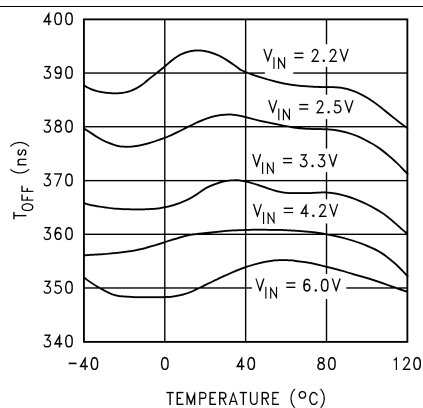
## 6.6 Typical Characteristics


**Figure 1. Enable Current vs  $V_{IN}$  (Device Switching)**

**Figure 2. Disable Current vs  $V_{IN}$  (Device Not Switching)**

**Figure 3.  $\overline{\text{SHDN}}$  Threshold vs  $V_{IN}$** 

**Figure 4. Switch Current Limit vs  $V_{IN}$** 

**Figure 5. Switch  $R_{DS(on)}$  vs  $V_{IN}$** 

**Figure 6. FB Trip Point and FB Pin Current vs Temperature**

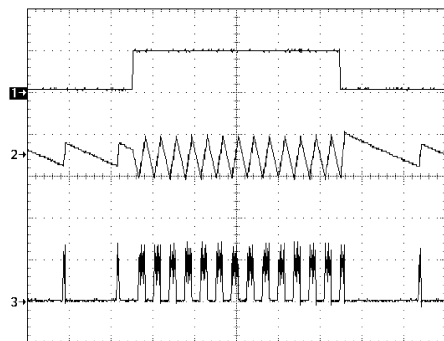
## Typical Characteristics (continued)



**Figure 7. Output Voltage vs Load Current**

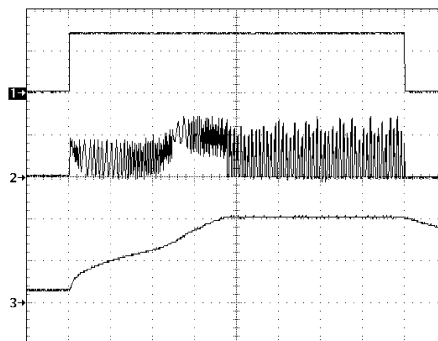


**Figure 8. Off Time vs Temperature**



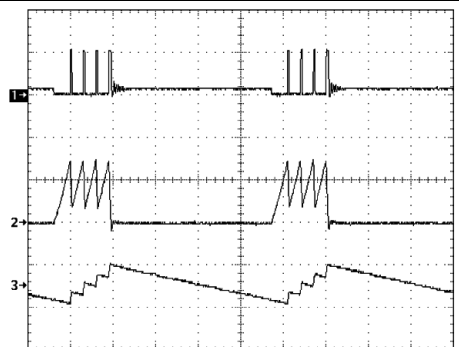
- 1) Load: 0.5 mA to 5 mA to 0.5 mA, DC  
 2)  $V_{OUT}$ : 200 mV/div, AC  
 3)  $I_L$ : 100 mA/div, DC
- $V_{OUT} = 20\text{ V}$   
 $V_{IN} = 3\text{ V}$   
 $T = 100\text{ }\mu\text{s/div}$

**Figure 9. Step Response**



- 1) SHDN: 1 V/div, DC  
 2)  $V_{OUT}$ : 10 V/div, AC  
 3)  $I_L$ : 100 mA/div, DC
- $V_{IN} = 3\text{ V}$   
 $T = 100\text{ }\mu\text{s/div}$   
 $V_{OUT} = 20\text{ V}$   
 $R_L = 3.9\text{ k}\Omega$

**Figure 10. Start-Up and Shutdown**



- 1)  $V_{SW}$ : 20 V/div, DC  
 2) Inductor Current: 100 mA/div, DC  
 3)  $V_{OUT}$ : 200 mV/div, AC
- $V_{IN} = 2.7\text{ V}$   
 $I_{OUT} = 2.5\text{ mA}$

$V_{OUT} = 20\text{ V}$

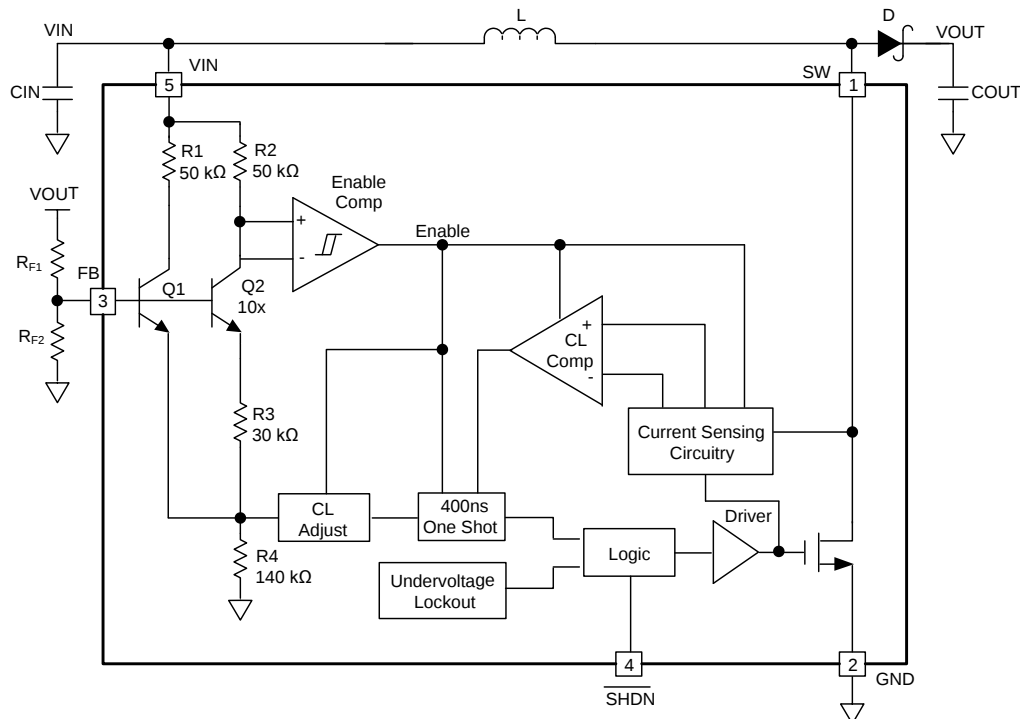
**Figure 11. Typical Switching Waveform**

## 7 Detailed Description

### 7.1 Overview

The LM2705 is a small boost converter utilizing a constant off time architecture. The device can provide up to 20.5 V at the output with up to 150 mA of peak switch current.

### 7.2 Functional Block Diagram



Copyright © 2016, Texas Instruments Incorporated

### 7.3 Feature Description

The LM2705 device features a constant off-time control scheme. Operation can be best understood by referring to [Functional Block Diagram](#) and [Figure 11](#). Transistors Q1 and Q2 and resistors R3 and R4 of [Functional Block Diagram](#) form a bandgap reference used to control the output voltage. When the voltage at the FB pin is less than 1.237 V, the Enable Comp in [Functional Block Diagram](#) enables the device, and the NMOS switch is turned on pulling the SW pin to ground. When the NMOS switch is on, current begins to flow through inductor L while the load current is supplied by the output capacitor  $C_{OUT}$ . Once the current in the inductor reaches the current limit, the CL comp trips, and the 400-ns one shot turns off the NMOS switch. The SW voltage then rises to the output voltage plus a diode drop, and the inductor current begins to decrease as shown in [Figure 11](#). During this time the energy stored in the inductor is transferred to  $C_{OUT}$  and the load. After the 400-ns off-time the NMOS switch is turned on, and energy is stored in the inductor again. This energy transfer from the inductor to the output causes a stepping effect in the output ripple as shown in [Figure 11](#).

This cycle is continued until the voltage at FB reaches 1.237 V. When FB reaches this voltage, the Enable Comp disables the device, turning off the NMOS switch and reducing the  $I_Q$  of the device to 40  $\mu A$ . The load current is then supplied solely by  $C_{OUT}$  indicated by the gradually decreasing slope at the output as shown in [Figure 11](#). When the FB pin drops slightly below 1.237 V, the Enable Comp enables the device and begins the cycle described previously.

### 7.4 Device Functional Modes

The  $\overline{SHDN}$  pin can be used to turn off the LM2705 and reduce the  $I_Q$  to 0.01  $\mu A$ . In shutdown mode the output voltage is a diode drop lower than the input voltage.

## 8 Application and Implementation

### NOTE

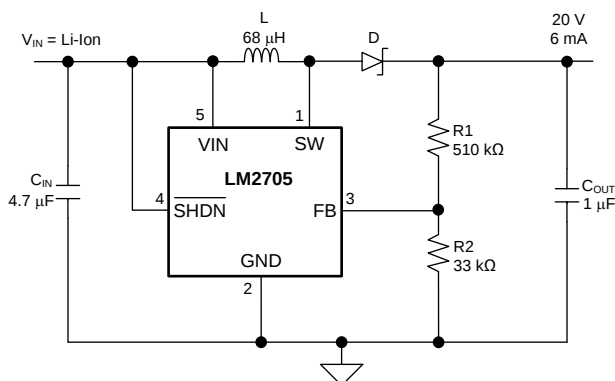
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The LM2705 is a 20-V boost designed for low power boost applications. Typical input voltage range makes this ideal for standard single cell Li+ batteries or 2 to 4 series alkaline batteries.

### 8.2 Typical Application

Figure 12 shows a typical Li+ voltage range to 20-V application. The 68-μH inductor allows for a low ripple current and high light-load efficiency.



Copyright © 2016, Texas Instruments Incorporated

**Figure 12. Typical 20-V Application**

#### 8.2.1 Design Requirements

For typical DC-DC converter applications, use the parameters listed in Table 1.

**Table 1. Design Parameters**

| DESIGN PARAMETER | EXAMPLE VALUE  |
|------------------|----------------|
| Input voltage    | 2.5 V to 4.2 V |
| Output voltage   | 12 V           |
| Output current   | up to 8 mA     |
| Inductor         | 33 μH          |

#### 8.2.2 Detailed Design Procedure

##### 8.2.2.1 Inductor Selection - Boost Regulator

The appropriate inductor for a given application is calculated using Equation 1:

$$L = \left( \frac{V_{OUT} - V_{IN(min)} + V_D}{I_{CL}} \right) T_{OFF}$$

where

- $V_D$  is the Schottky diode voltage
- $I_{CL}$  is the switch current limit found in the [Typical Characteristics](#)

- $T_{OFF}$  is the switch off time (1)

When using this equation be sure to use the minimum input voltage for the application, such as for battery powered applications. For the LM2705 constant-off time control scheme, the NMOS power switch is turned off when the current limit is reached. There is approximately a 100-ns delay from the time the current limit is reached in the NMOS power switch and when the internal logic actually turns off the switch. During this 100-ns delay, the peak inductor current increases. This increase in inductor current demands a larger saturation current rating for the inductor. This saturation current can be approximated by [Equation 2](#):

$$I_{PK} = I_{CL} + \left( \frac{V_{IN(max)}}{L} \right) 100 \text{ ns} \quad (2)$$

Choosing inductors with low ESR decrease power losses and increase efficiency.

Take care when choosing an inductor. For applications that require an input voltage that approaches the output voltage, such as when converting a Li-Ion battery voltage to 5 V, the 400-ns off time may not be enough time to discharge the energy in the inductor and transfer the energy to the output capacitor and load. This can cause a ramping effect in the inductor current waveform and an increased ripple on the output voltage. Using a smaller inductor causes the  $I_{PK}$  to increase and increases the output voltage ripple further.

For typical curves and evaluation purposes the DT1608C series inductors from Coilcraft were used. Other acceptable inductors include, but are not limited to, the SLF6020T series from TDK, the NP05D series from Taiyo Yuden, the CDRH4D18 series from Sumida, and the P1166 series from Pulse.

### 8.2.2.2 Inductor Selection - SEPIC Regulator

[Equation 3](#) can be used to calculate the approximate inductor value for a SEPIC regulator:

$$L2 = 2 \left( \frac{V_{OUT} + V_D}{I_{CL}} \right) T_{OFF} \quad (3)$$

The boost inductor, L1, can be smaller or larger but is generally chosen to be the same value as L2. See [Figure 23](#) and [Figure 24](#) for typical SEPIC applications.

### 8.2.2.3 Diode Selection

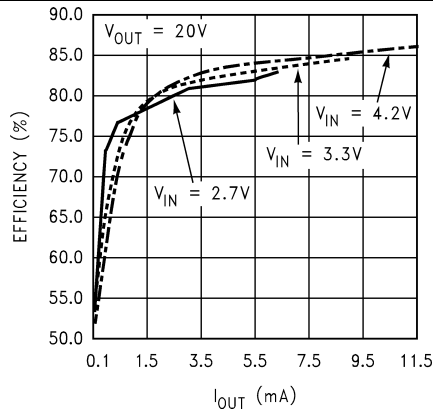
To maintain high efficiency, the average current rating of the Schottky diode should be larger than the peak inductor current,  $I_{PK}$ . Schottky diodes with a low forward drop and fast switching speeds are ideal for increasing efficiency in portable applications. Choose a reverse breakdown of the Schottky diode larger than the output voltage.

### 8.2.2.4 Capacitor Selection

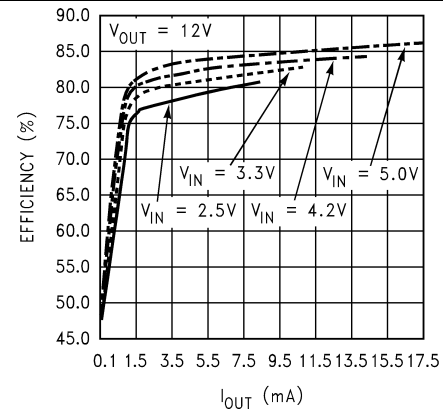
Choose low equivalent series resistance (ESR) capacitors for the output to minimize output voltage ripple. Multilayer ceramic capacitors are the best choice. For most applications, a 1-μF ceramic capacitor is sufficient. For some applications a reduction in output voltage ripple can be achieved by increasing the output capacitor. Output voltage ripple can further be reduced by adding a 4.7-pF feed-forward capacitor in the feedback network placed in parallel with RF1 (see [Functional Block Diagram](#)).

Local bypassing for the input is needed on the LM2705. Multilayer ceramic capacitors are a good choice for this as well. A 4.7-μF capacitor is sufficient for most applications. For additional bypassing, a 100-nF ceramic capacitor can be used to shunt high frequency ripple on the input.

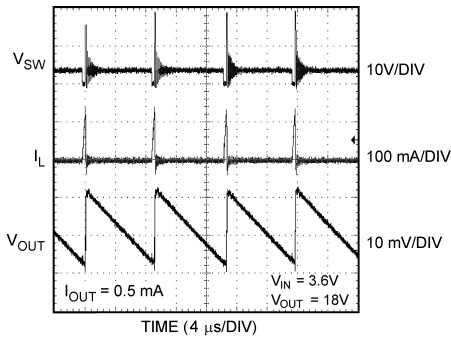
## 8.2.3 Application Curves



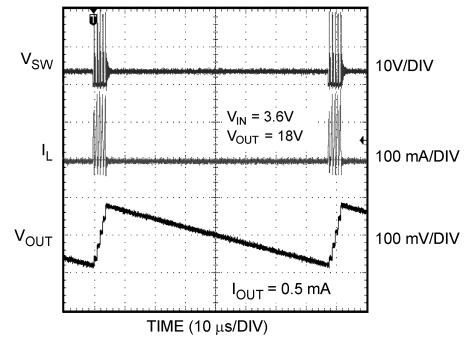
**Figure 13. Efficiency vs Load Current**



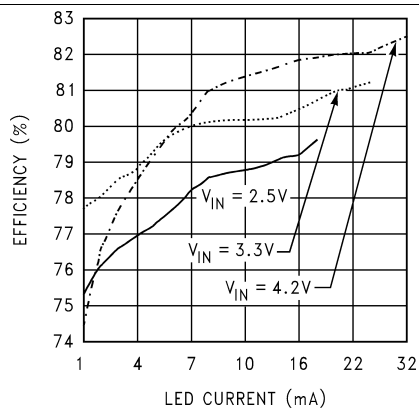
**Figure 14. Efficiency vs Load Current**



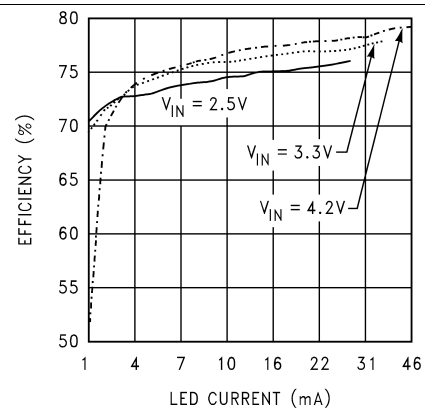
**Figure 15. Output Ripple Voltage  
Copt, Ropt Included**



**Figure 16. Output Ripple Voltage  
Copt, Ropt Excluded**



**Figure 17. Two White-LED Efficiency**



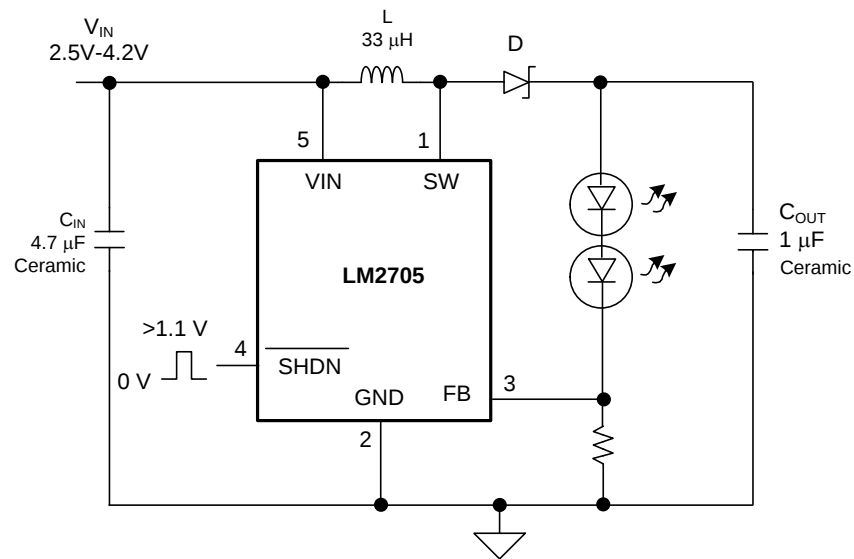
**Figure 18. Three White-LED Efficiency**

## LM2705

SNVS191F –NOVEMBER 2002–REVISED OCTOBER 2016

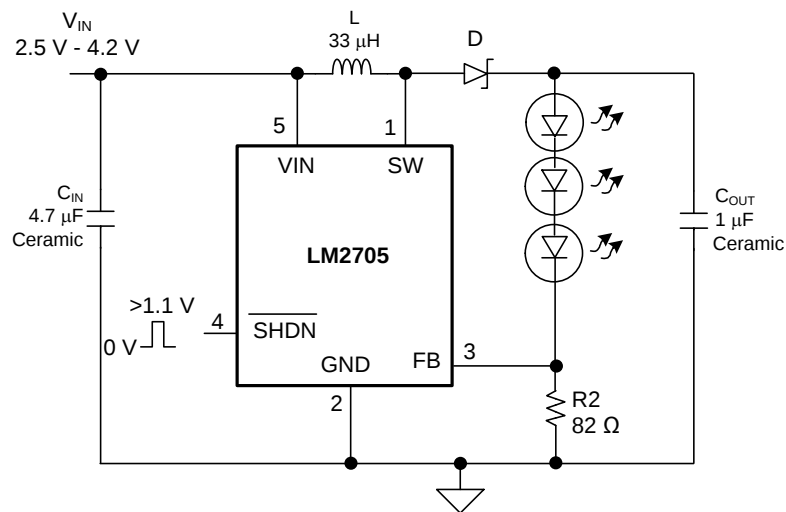
www.ti.com

### 8.3 Additional Applications



Copyright © 2016, Texas Instruments Incorporated

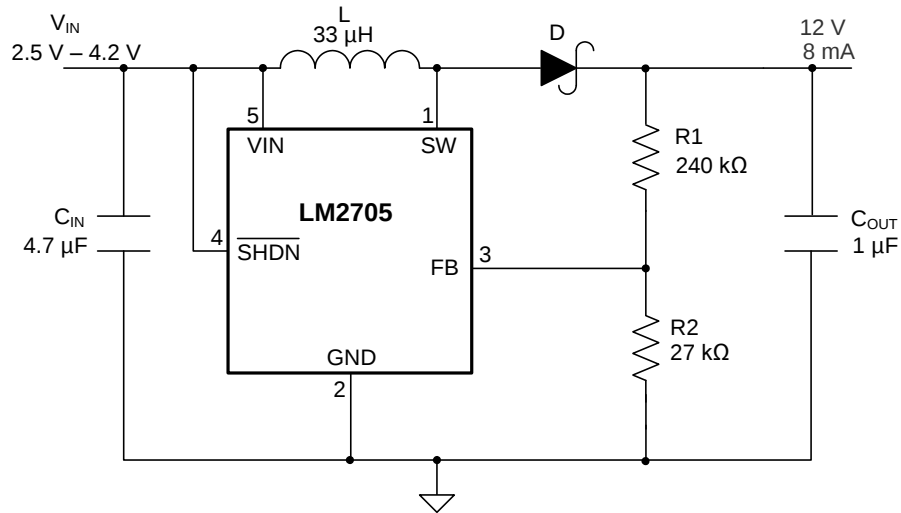
**Figure 19. Two White-LED Application**



Copyright © 2016, Texas Instruments Incorporated

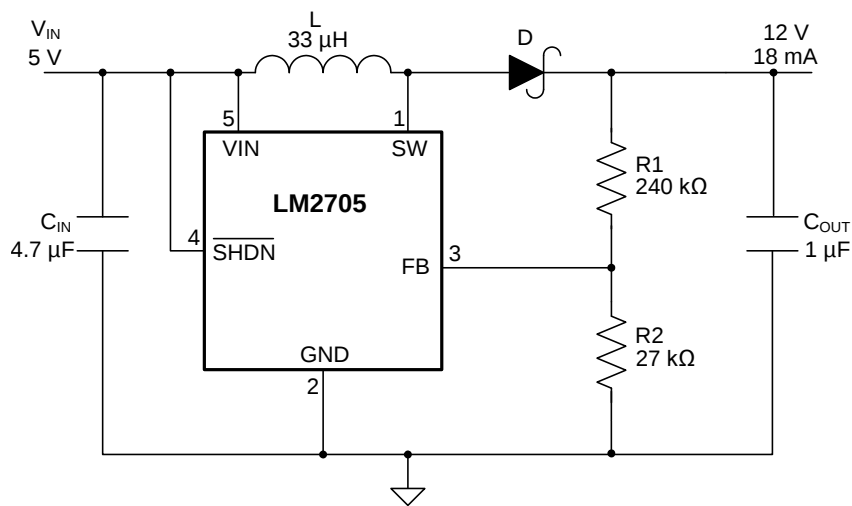
**Figure 20. Three White-LED Application**

## Additional Applications (continued)



Copyright © 2016, Texas Instruments Incorporated

**Figure 21. Li-Ion 12-V Application**



Copyright © 2016, Texas Instruments Incorporated

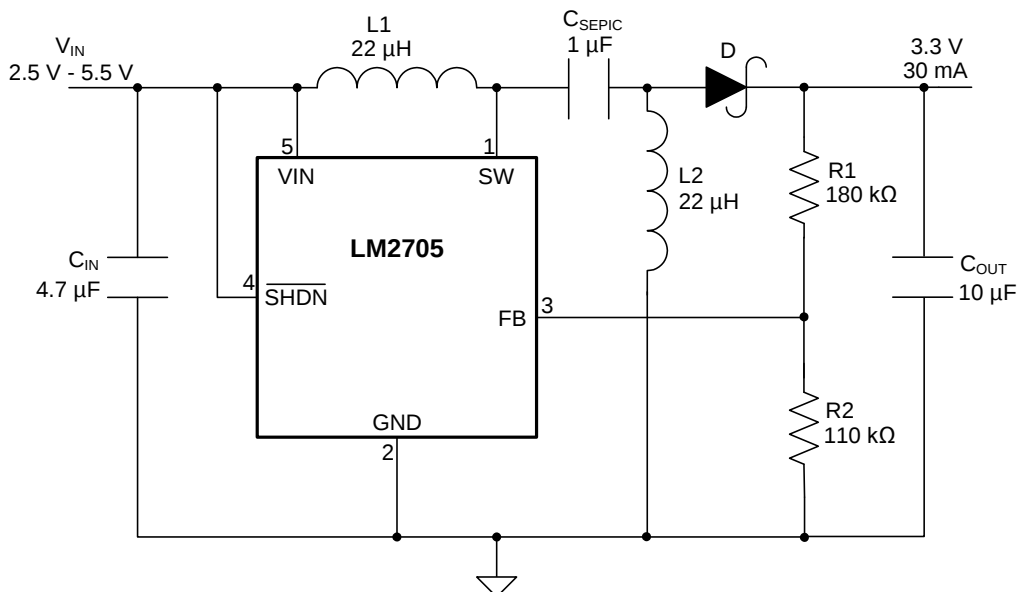
**Figure 22. 5-V to 12-V Application**

## LM2705

SNVS191F – NOVEMBER 2002 – REVISED OCTOBER 2016

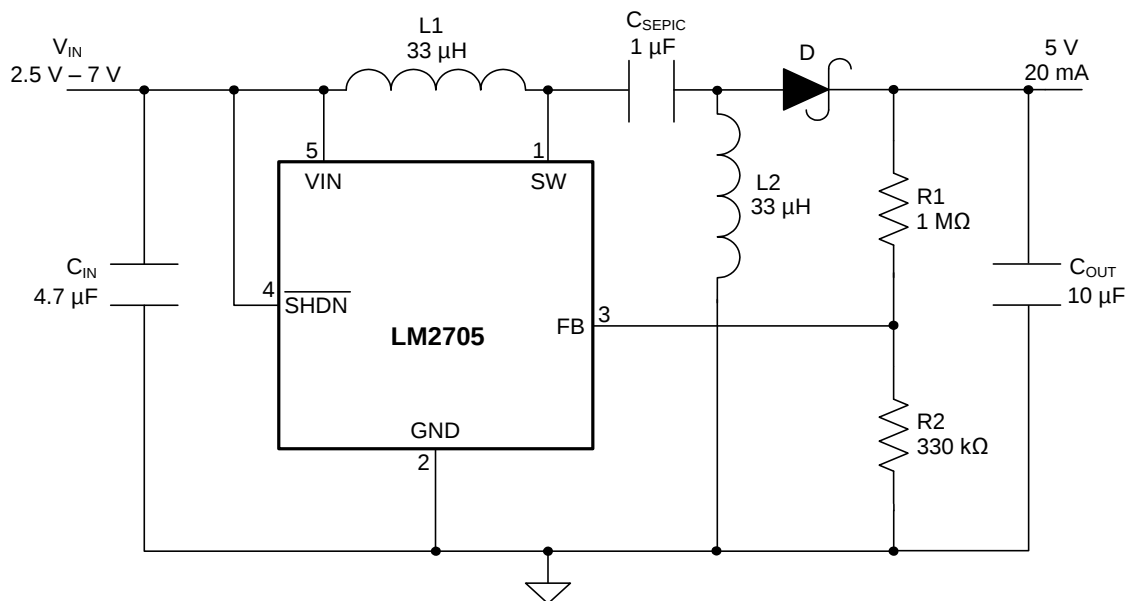
[www.ti.com](http://www.ti.com)

### Additional Applications (continued)



Copyright © 2016, Texas Instruments Incorporated

**Figure 23. 3.3-V SEPIC Application**



Copyright © 2016, Texas Instruments Incorporated

**Figure 24. 5-V SEPIC Application**

## 9 Power Supply Recommendations

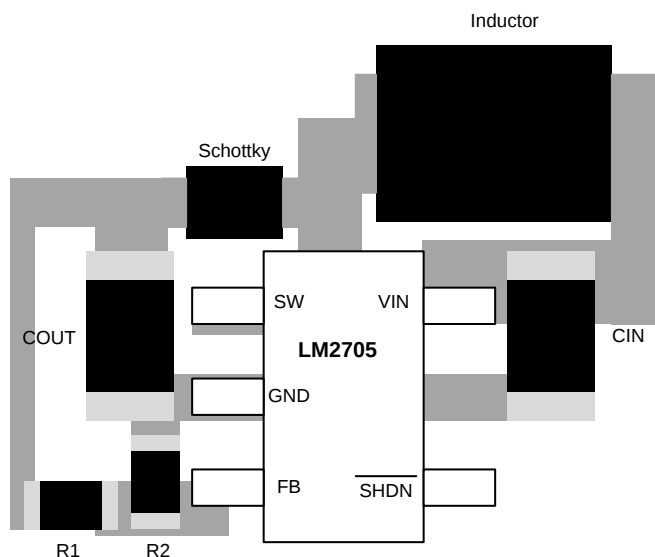
The LM2705 is designed to operate from an input voltage supply range from 2.2 V to 7 V. This input supply must be well regulated and capable to supply the required input current. If the input supply is located far from the LM2705, additional bulk capacitance may be required in addition to the ceramic bypass capacitors.

## 10 Layout

### 10.1 Layout Guidelines

The input bypass capacitor  $C_{IN}$ , as shown in Figure 25, must be placed close to the device. This reduces copper trace resistance, which effects input voltage ripple of the LM2705 device. For additional input voltage filtering, a 100-nF bypass capacitor can be placed in parallel with  $C_{IN}$  to shunt any high frequency noise to ground. The output capacitor,  $C_{OUT}$ , must also be placed close to the device. Any copper trace connections for the  $C_{OUT}$  capacitor can increase the series resistance, which directly effects output voltage ripple. Keep the feedback network, resistors R1 and R2, close to the FB pin to minimize copper trace connections that can inject noise into the system. The ground connection for the feedback resistor network must connect directly to an analog ground plane. Tie the analog ground plane directly to the GND pin. If no analog ground plane is available, the ground connection for the feedback network must tie directly to the GND pin. Minimize trace connections made to the inductor and Schottky diode to reduce power dissipation and increase overall efficiency.

### 10.2 Layout Example



**Figure 25. LM2705 Layout Example**

## 11 Device and Documentation Support

### 11.1 Device Support

#### 11.1.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

#### 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.4 Trademarks

E2E is a trademark of Texas Instruments.  
All other trademarks are the property of their respective owners.

#### 11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 11.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## PACKAGING INFORMATION

| Orderable Device   | Status<br>(1) | Package Type | Package<br>Drawing | Pins | Package<br>Qty | Eco Plan<br>(2)            | Lead/Ball Finish<br>(6) | MSL Peak Temp<br>(3) | Op Temp (°C) | Device Marking<br>(4/5) | Samples                 |
|--------------------|---------------|--------------|--------------------|------|----------------|----------------------------|-------------------------|----------------------|--------------|-------------------------|-------------------------|
| LM2705MF-ADJ       | NRND          | SOT-23       | DBV                | 5    |                | TBD                        | Call TI                 | Call TI              | -40 to 85    | S59B                    |                         |
| LM2705MF-ADJ/NOPB  | ACTIVE        | SOT-23       | DBV                | 5    | 1000           | Green (RoHS<br>& no Sb/Br) | CU SN                   | Level-1-260C-UNLIM   | -40 to 85    | S59B                    | <a href="#">Samples</a> |
| LM2705MFX-ADJ/NOPB | ACTIVE        | SOT-23       | DBV                | 5    | 3000           | Green (RoHS<br>& no Sb/Br) | CU SN                   | Level-1-260C-UNLIM   | -40 to 85    | S59B                    | <a href="#">Samples</a> |

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

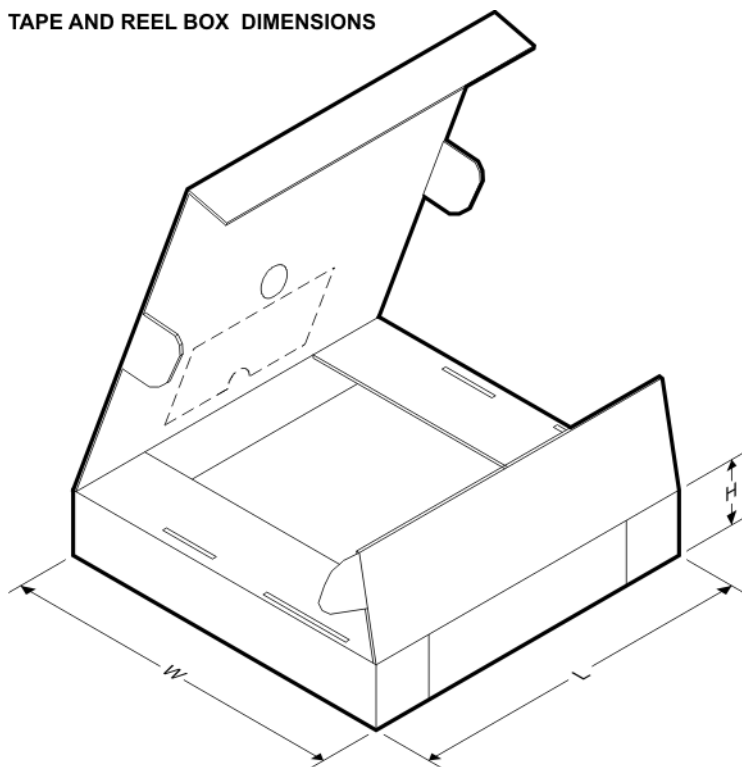


**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

| Device             | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| LM2705MF-ADJ/NOPB  | SOT-23       | DBV             | 5    | 1000 | 178.0              | 8.4                | 3.2     | 3.2     | 1.4     | 4.0     | 8.0    | Q3            |
| LM2705MFX-ADJ/NOPB | SOT-23       | DBV             | 5    | 3000 | 178.0              | 8.4                | 3.2     | 3.2     | 1.4     | 4.0     | 8.0    | Q3            |

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

| Device             | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|--------------------|--------------|-----------------|------|------|-------------|------------|-------------|
| LM2705MF-ADJ/NOPB  | SOT-23       | DBV             | 5    | 1000 | 210.0       | 185.0      | 35.0        |
| LM2705MFX-ADJ/NOPB | SOT-23       | DBV             | 5    | 3000 | 210.0       | 185.0      | 35.0        |

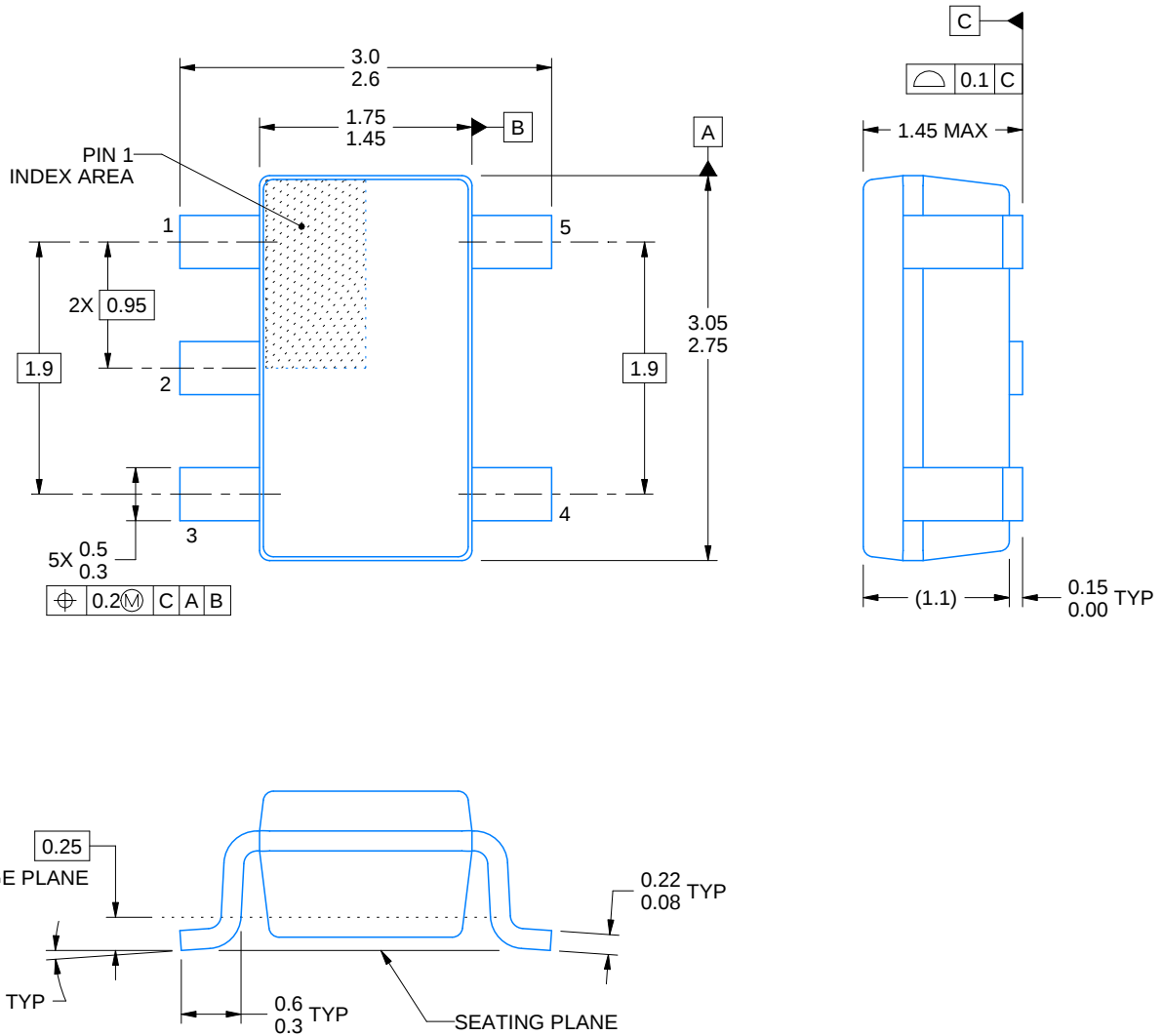


**DBV0005A**

## PACKAGE OUTLINE

**SOT-23 - 1.45 mm max height**

SMALL OUTLINE TRANSISTOR



4214839/D 11/2018

### NOTES:

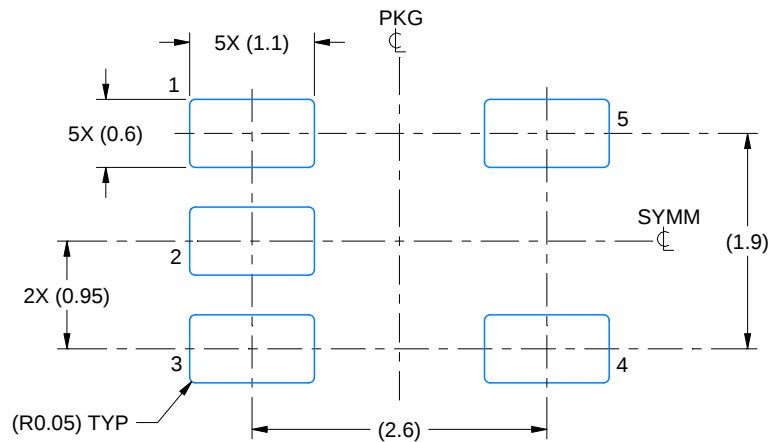
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.

# EXAMPLE BOARD LAYOUT

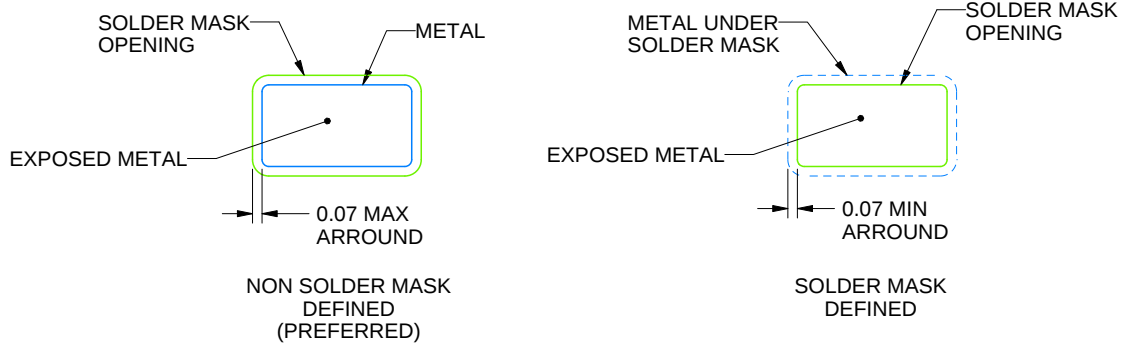
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214839/D 11/2018

NOTES: (continued)

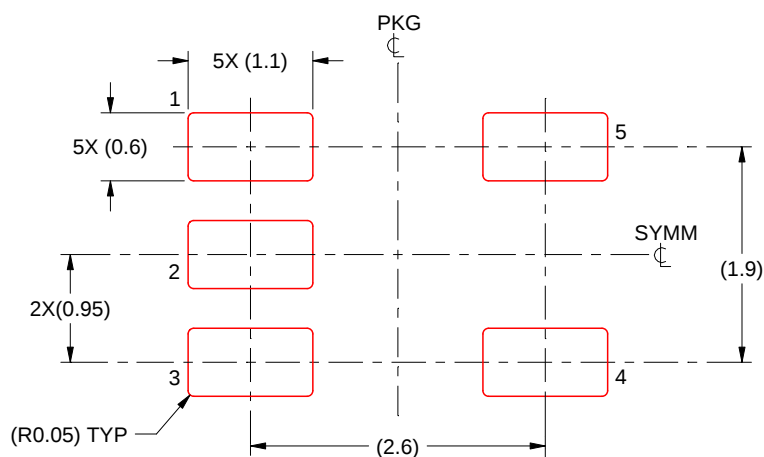
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

## EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4214839/D 11/2018

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

## IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale ([www.ti.com/legal/termsofsale.html](http://www.ti.com/legal/termsofsale.html)) or other applicable terms available either on [ti.com](http://ti.com) or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
Copyright © 2019, Texas Instruments Incorporated